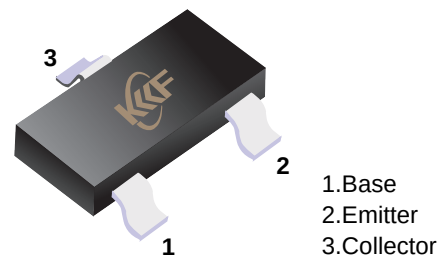


2SB1197

Low Frequency Transistor

Features

- Low $V_{CE(sat)}$, $V_{CE(sat)} \leq -0.5V$ ($I_C / I_B = -0.5A / -50mA$).
- $I_C = -0.8A$.
- PNP silicon transistor



■ Simplified outline(SOT-23)

Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base Voltage	V_{CBO}	-40	V
Collector-emitter Voltage	V_{CEO}	-32	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector current	I_C	-0.8	A
Collector power dissipation	P_C	0.2	W
Jumction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics $T_a = 25^\circ C$

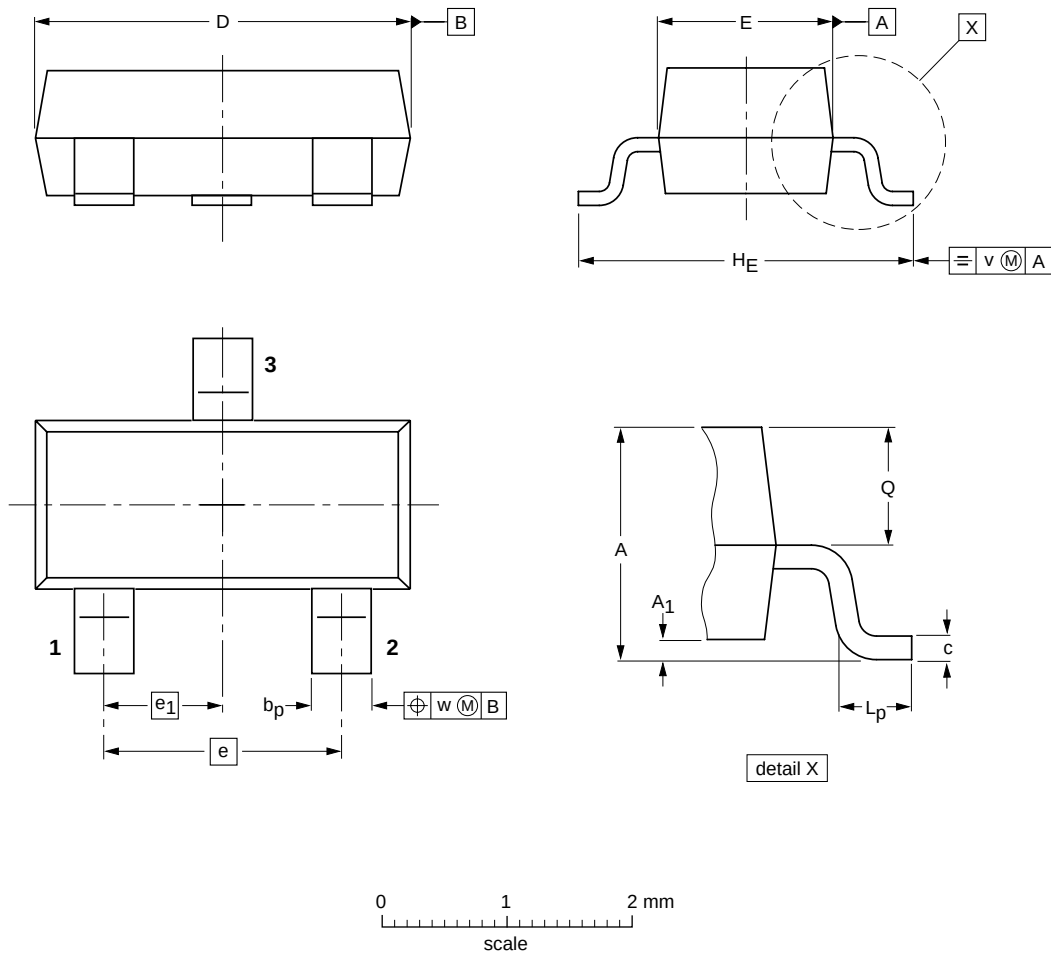
Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltae	V_{CBO}	$I_C = -50 \mu A$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1mA$	-32			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -50 \mu A$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20V$			-0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4V$			-0.5	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -0.5A, I_B = -50mA$			-0.5	V
DC current transfer ratio	h_{FE}	$V_{CE} = -3V, I_C = -100mA$	120		390	
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		12	30	pF
Transition frequency	f_T	$V_{CE} = -5V, I_E = 50mA, f = 100MHz$		200		MHz

h_{FE} Classification

Marking	AHQ	AHR
Rank	Q	R
h_{FE}	120~270	180~390

2SB1197

■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1